

# RJK5013DPE

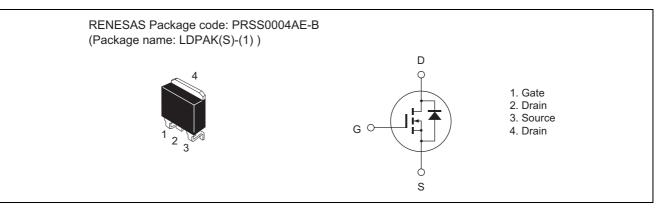
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1488-0200 Rev.2.00 Nov 29, 2006

# Features

- Low on-resistance
- Low leakage current
- High speed switching

# Outline



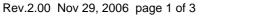
# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to source voltage V<sub>DSS</sub> 500 V V Gate to source voltage V<sub>GSS</sub> ±30 14 A Drain current  $I_D$ Note1 Drain peak current 42 А Body-drain diode reverse drain current  $I_{DR}$ 14 А 42 Body-drain diode reverse drain peak current А I<sub>DR (pulse)</sub> I<sub>AP</sub><sup>Note3</sup> Avalanche current 4 A E<sub>AR</sub><sup>Note3</sup> 0.88 Avalanche energy mJ Pch Note2 W Channel dissipation 100 Channel to case thermal impedance θch-c 1.25 °C/W Channel temperature Tch 150 °C °C Storage temperature Tstg -55 to +150

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C





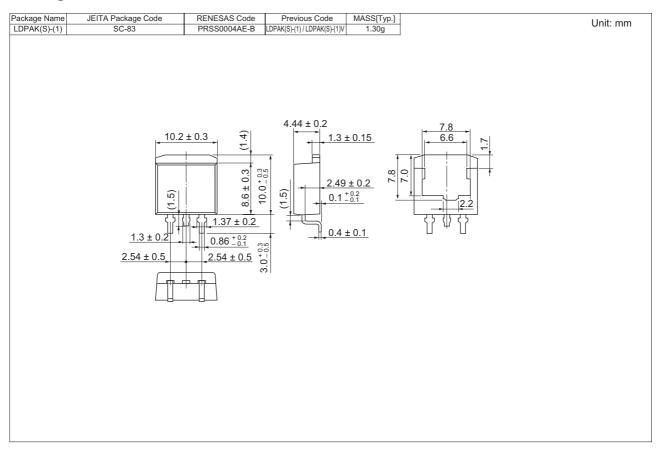
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		—	1	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		—	±0.1	μΑ	$V_{GS}$ = ±30 V, $V_{DS}$ = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>		0.385	0.465	Ω	$I_D = 7 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1450	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	155	—	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	19	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	34	—	ns	I <sub>D</sub> = 7 A
Rise time	tr	_	24	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>		86	—	ns	R <sub>L</sub> = 35.7 Ω Rg = 10 Ω
Fall time	t <sub>f</sub>		16	—	ns	
Total gate charge	Qg		38	_	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs		8	—	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 14 A
Gate to drain charge	Qgd	_	17	—	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.9	1.5	V	$I_F = 14 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		310		ns	$I_F = 14 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test



# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
RJK5013DPE-00-J3	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



# RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Benesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
  Pines
  This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warranties or representations with respect to the accuracy or completeness of the information in this document.
  But not infinited to, product data. diagrams, charts, programs, algorithms, and application scule as the development of weapons of mass and regulations, and proceedures required by such laws and regulation.
  All information in the purpose of any other military use. When exporting the products or the technology described herein, you should follow the applicable export control laws and regulations, and proceedures required by such laws and regulations.
  All information included in this document, such as product data, diagrams, charts, programs, algorithms, and application oracit useraphes, is current as of the date this document, but has product data, diagrams, charts, programs, algorithms, and application is activated in this document, but has product data, diagrams, charts, programs, algorithms, and application is additional and different information in the date this document, but Renesas assumes no liability whattosever for any damages incurred as a constraint of the data different information in this document, but Renesas assumes no liability whattosever for any damages incurred as a different information in this document, but Renesas as products are not eleval and product data. Has a state and the data different information in the data different information includ



### **RENESAS SALES OFFICES**

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

## Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

http://www.renesas.com